

Semiconductors
High-reliability discrete products and engineering services since 1977

## BU204-BU205

NPN POWER TRANSISTORS

## FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS ( $\mathrm{Sn} / \mathrm{Pb}$ plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

| Characteristic | Symbol | BU204 | BU205 | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Collector-Emitter Voltage | $V_{\text {ceo }}$ | 600 | 700 | V |
| Collector-Emitter Voltage | $\mathrm{V}_{\text {CEX }}$ | 1300 | 1500 | V |
| Emitter-Base Voltage | $V_{\text {Ebo }}$ | 5.0 |  | V |
| Collector Current - continuous Peak | Ic | $\begin{aligned} & 2.5 \\ & 3.0 \end{aligned}$ |  | A |
| Base Current -continuous | $\mathrm{I}_{\mathrm{B}}$ | 1.0 |  | A |
| Total Power Dissipation @ $\mathrm{T}_{\mathrm{C}}=\mathbf{2 5 ^ { \circ }} \mathrm{C}$ Derate Above $25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{D}}$ | 36 |  | $\begin{gathered} \mathrm{W} \\ \mathrm{~W} /{ }^{\circ} \mathrm{C} \end{gathered}$ |
| Operating and Storage Temperature Range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -65 to +115 |  | ${ }^{\circ} \mathrm{C}$ |
| Thermal Resistance, Junction to Case | $\mathrm{R}_{\text {eJc }}$ | 2.5 |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

ELECTRICAL CHARACTERISTICS ( $\mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Characteristic |  |  | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-Emitter Sustaining Voltage ${ }^{(1)}$$\left(\mathrm{I}_{\mathrm{C}}=100 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=0\right)$ |  | $\begin{aligned} & \hline \text { BU204 } \\ & \text { BU205 } \end{aligned}$ | $V_{\text {ceo(sus) }}$ | $\begin{aligned} & 600 \\ & 700 \end{aligned}$ |  | V |
| Collector Cutoff Current$\begin{aligned} & \left(\mathrm{V}_{\mathrm{CE}}=1300 \mathrm{~V}, \mathrm{~V}_{\mathrm{BE}}=0\right) \\ & \left(\mathrm{V}_{\mathrm{CE}}=1500 \mathrm{~V}, \mathrm{~V}_{\mathrm{BE}}=0\right) \end{aligned}$ |  | $\begin{aligned} & \text { BU204 } \\ & \text { BU205 } \end{aligned}$ | Ices | - | $\begin{aligned} & 1.0 \\ & 1.0 \end{aligned}$ | mA |
| Emitter Cutoff Current$\left(\mathrm{V}_{\mathrm{EB}}=5.0 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=0\right)$ |  |  | $\mathrm{I}_{\text {Ebo }}$ | - | 10 | mA |
| DC Current Gain ${ }^{(1)}$$\left(\mathrm{I}_{\mathrm{C}}=2.0 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{~V}\right)$ |  |  | $h_{\text {fe }}$ | 15 | 60 | - |
| Collector-Emitter Saturation Voltage ${ }^{(1)}$$\left(\mathrm{I}_{\mathrm{C}}=2.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=1.0 \mathrm{~A}\right)$ |  |  | $\mathrm{V}_{\text {CE(sat) }}$ | - | 5.0 | V |
| Base-Emitter Saturation Voltage ${ }^{(1)}$$\left(\mathrm{I}_{\mathrm{C}}=2.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=1.0 \mathrm{~A}\right)$ |  |  | $\mathrm{V}_{\text {BE(sat) }}$ | - | 1.5 | V |
| Current Gain - Bandwidth Product ( $\mathrm{Ic}=100 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=5 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ ) |  |  | $\mathrm{f}_{\text {T }}$ |  |  | MHz |
| Output Capacitance$\left(\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0, \mathrm{f}=1.0 \mathrm{MHz}\right)$ |  |  | Cob |  |  | pF |
| Fall Time | $\mathrm{I}_{\mathrm{C}}=2.0 \mathrm{~A}, \mathrm{I}_{\mathrm{B} 1} 1.0 \mathrm{~A}, \mathrm{~L}_{\mathrm{B}}=25 \mathrm{uH}$ |  | $\mathrm{t}_{\mathrm{f}}$ |  |  | $\mu \mathrm{s}$ |

Note 1: Pulse test: Pulse width $\leq 300 \mu \mathrm{~s}$. Duty cycle $\leq 2 \%$.

IGITRON
Semiconductors
High-reliability discrete products and engineering services since 1977

BU204-BU205

NPN POWER TRANSISTORS

MECHANICAL CHARACTERISTICS

| Case: | TO-3 |
| :--- | :--- |
| Marking: | Alpha-Numeric |
| Polarity: | See below |



|  | TO-3 |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  | Inches |  | Millimeters |  |
|  | Min | Max | Min | Max |
| CD | - | 0.875 | - | 22.220 |
| CH | 0.250 | 0.380 | 6.860 | 9.650 |
| HT | 0.060 | 0.135 | 1.520 | 3.430 |
| BW | - | 1.050 | - | 26.670 |
| HD | 0.131 | 0.188 | 3.330 | 4.780 |
| LD | 0.038 | 0.043 | 0.970 | 1.090 |
| LL | 0.312 | 0.500 | 7.920 | 12.700 |
| BL | 1.550 REF | 39.370 REF |  |  |
| MHS | 1.177 | 1.197 | 29.900 | 30.400 |
| PS | 0.420 | 0.440 | 10.670 | 11.180 |
| S1 | 0.655 | 0.675 | 16.640 | 17.150 |

FIGURE -1 POWER DERATING


IGITRON
Semiconductors
High-reliability discrete products and engineering services since 1977

BU204-BU205

NPN POWER TRANSISTORS


FORWARD BIAS SAFE OPERATING AREA


